

An X-band GaN PA MMIC for Phased Array Radar Applications

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Abstract

Active phased array radars require numerous Power Amplifiers (PAs), which must be small, efficient and low-cost. This paper describes an X-band PA MMIC that covers 9 to 11.5GHz and satisfies these requirements. It has an output power of 7W (38.5dBm) from a 29dBm drive with a Power Added Efficiency (PAE) of 42%. The design was realized on the 0.25 μ m gate length GaN on SiC process of UMS (GH25) using Keysight's ADS 2015. The die size is just 1.5mm x 2mm, which means around 2,300 PAs can be fabricated on a single 4" diameter wafer.

Introduction

Phased array radars use many transmitters operating in parallel to generate a high total transmitted RF power level. The RF amplifier at the output of each transmitter must be capable of generating the required RF power and must do so efficiently and at an acceptable cost. The elements must be closely spaced (normally around a half wavelength separation) and this fact, coupled with the potentially huge level of total dissipated power, can represent enormous challenges for the radar design team. The PA is normally the key contributor to the power dissipation so a component with high efficiency is very desirable.

Typical RF power levels required from each transmitting element are in the range 5 to 10W. GaN technology can realise such power levels with ease and can do so with high efficiency. The amplifier described here was designed to realise the output stage with adequate gain to allow the input drive to be provided by readily available COTS technology. The target performance requirements for the amplifier are listed in Table 1.

Parameter	Value	Units
Frequency	9 - 11	GHz
Small signal gain	> 12	dB
Psat	> 6	W
	> 37.7	dBm
PAE at Psat	> 40	%
Vdd	25	V

Table 1: Target Performance Requirements for the PA

Design and Layout

The PA was designed for realisation on the 0.25 μm gate length GaN on SiC process of UMS (GH25). The design process commenced with simulations at the transistor level to determine the preferred transistor size and bias. The RF output power that a transistor can generate increases as the total gate periphery increases. However, as the physical size of the transistor starts to become electrically significant both the large signal and small signal performance will start to degrade as a result of distributed parasitics. Microwave frequency PAs normally make use of multiple power combined transistors for this very reason and the impact on performance of the transistor's size must be carefully considered.

Another factor to consider in selecting the optimum transistor size is the range of validity of the transistor models. Commercial foundries normally have Process Design Kits (PDKs) that include scaleable transistor models. Whilst the models may allow arbitrary adjustment of gate width and number of fingers, the models will be based on data from a selection of transistors of discrete sizes. It is best to try and select a transistor size that does not require too much extrapolation from the sizes of transistors used to generate the models.

With these factors in mind an 8x150 μm transistor was selected for the planned design. The recommended V_{ds} for GH25 transistors is 25V; simulations were undertaken comparing P_{sat} , PAE, and available gain at various quiescent bias currents. Figure 1 shows an example set of load-pull contours. The P_{sat} (at 4dB compression) for the selected transistor size was around 36.5dBm (4.4W) and varied only modestly with the quiescent bias. The PAE improved with reducing quiescent bias current but the small signal gain decreased. The design was progressed with a quiescent bias currents I_{ds} of 45mA (37.5mA/mm); the performance with a higher bias current of 90mA (75mA/mm) was reviewed during the design process to assess the performance benefits that a higher bias current could potentially offer.

A design with two power combined 8x150 μm transistors was progressed. Allowing for the losses of the on-chip biasing and matching networks, this would still allow the target 6W (37.7dBm) minimum output power requirement to be exceeded.

Further detailed load-pull simulations were then undertaken on the selected transistor. The power delivered to the load at 4dB compression was plotted against PAE at 10GHz for a range of load impedances (Figure 2). Each trace in Figure 2 represents a constant real part of the load impedance with a varying imaginary part. This analysis was used to select the optimum load impedance of 11.25 + j21.67 Ω that was used as the target during the design process.

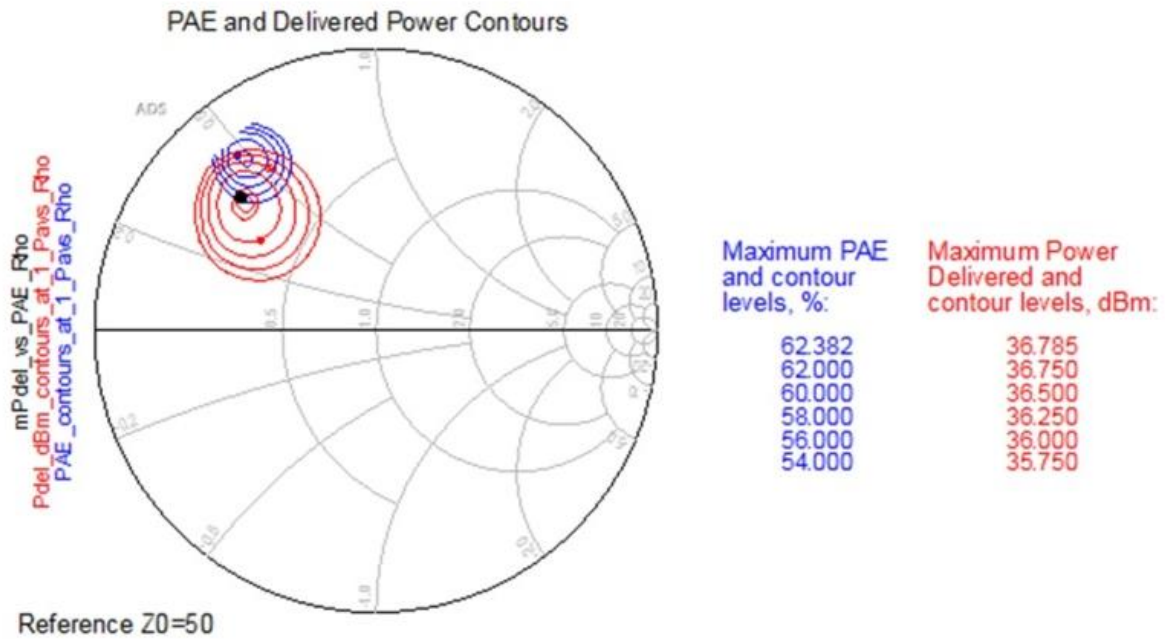


Figure 1: Load-pull simulations on the 8x150µm transistor using ADS 2015

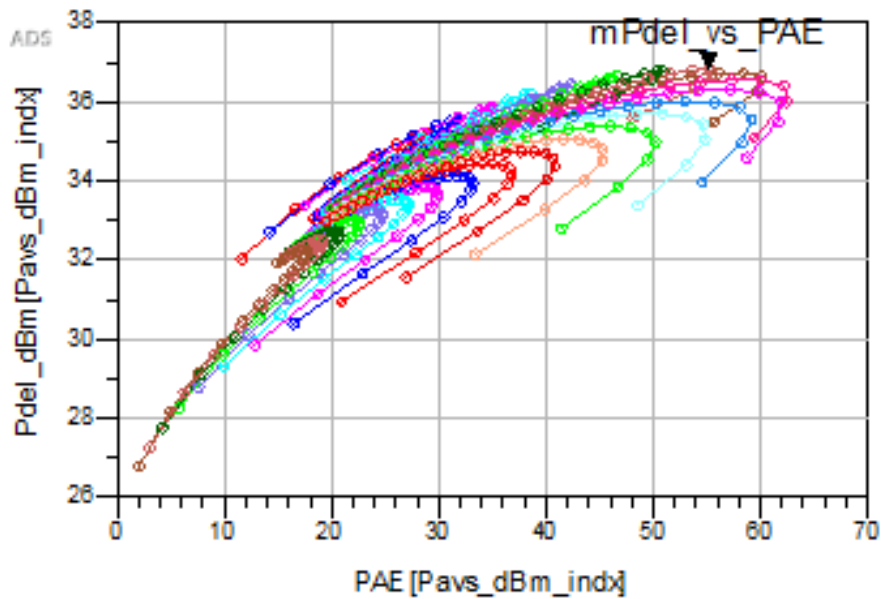


Figure 2: Simulated PAE and Pout for various fundamental load impedances

The design approach was to power combine the RF outputs of two of the selected transistor. Throughout the design process effort was expended on ensuring that the die area was minimized. This can be clearly seen from the layout plot reproduced in Figure 3.

Duplicate on-chip drain biasing networks are included at top and bottom of the IC. This preserves symmetry and allows the PA to be biased from either side. The transmission line used to provide the

drain bias is also used as inductive matching at the drain of each transistor to allow the optimum inductive load impedance to be presented to the transistor.

High impedance series lines are used at each transistor output to transform the common 50Ω load impedance at the output of the PA to the lower impedance required at the transistors' drains to present the optimum real part of the load at each transistor output.

The input matching network is a low-pass structure that transforms the low impedance at the transistors' input to a 50Ω impedance at the PA input. On-chip balancing resistors are included between the two PA channels to ensure odd-mode stability. On-chip RC de-coupling is included at both gate and drain to ensure low frequency stability where the GaN transistors have a very high level of available gain.

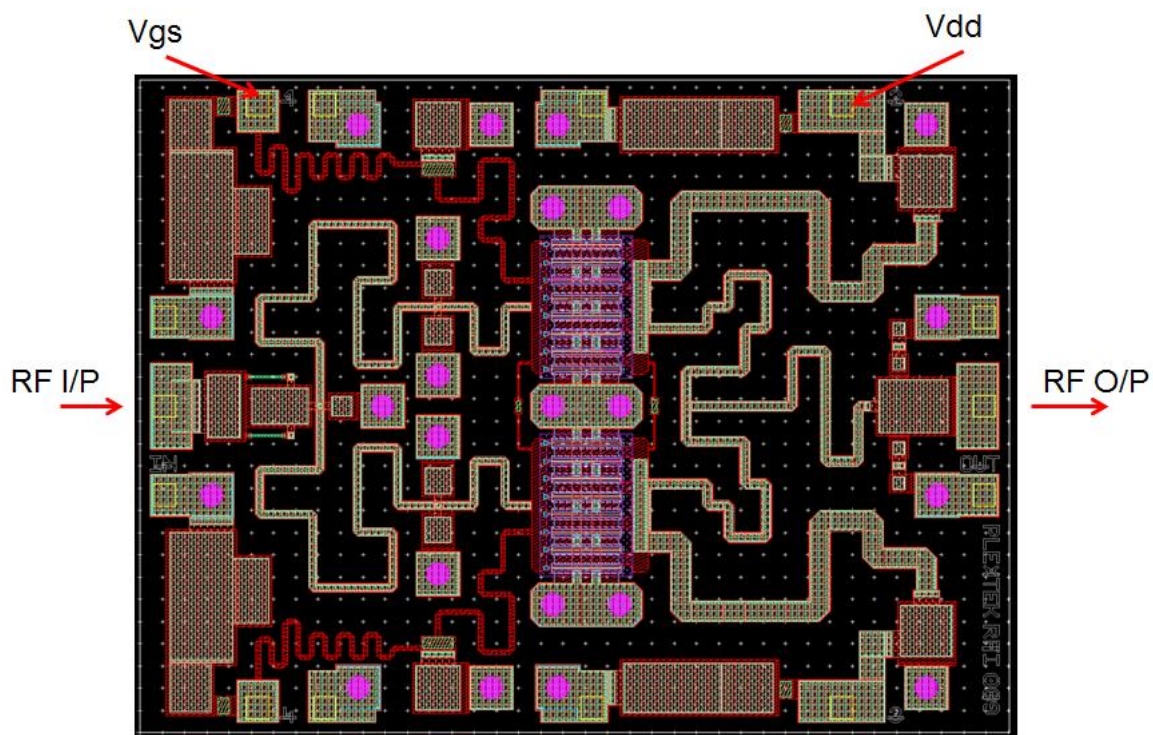


Figure 3: Layout plot of the X-band GaN PA

Realisation and Measured Performance

A photograph of one of the PA die is shown in Figure 4. The die measures just 1.5mm x 2mm, which means that a single 4" diameter wafer should contain around 2,300 amplifier ICs.

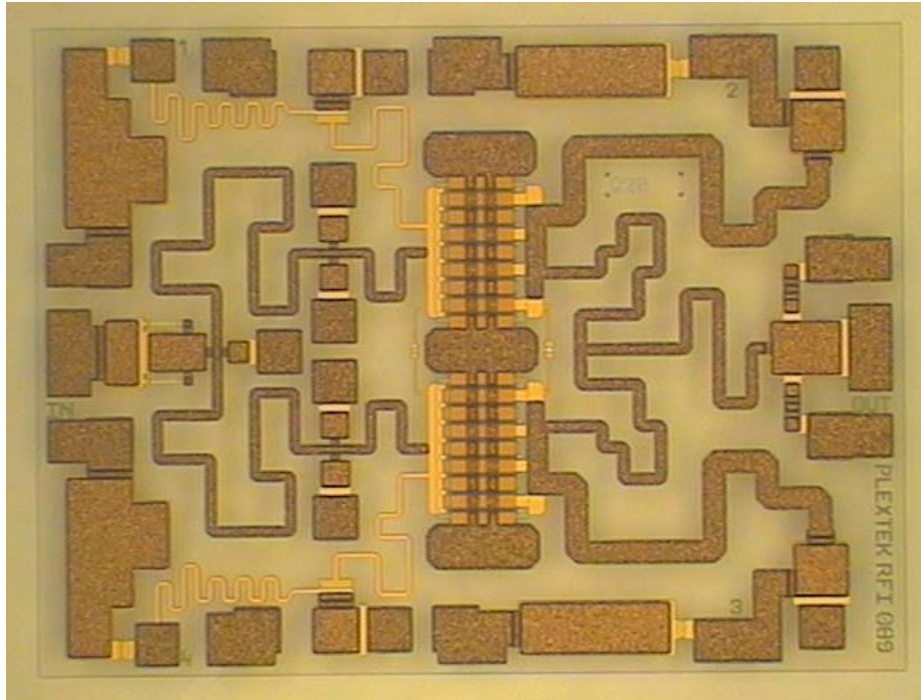
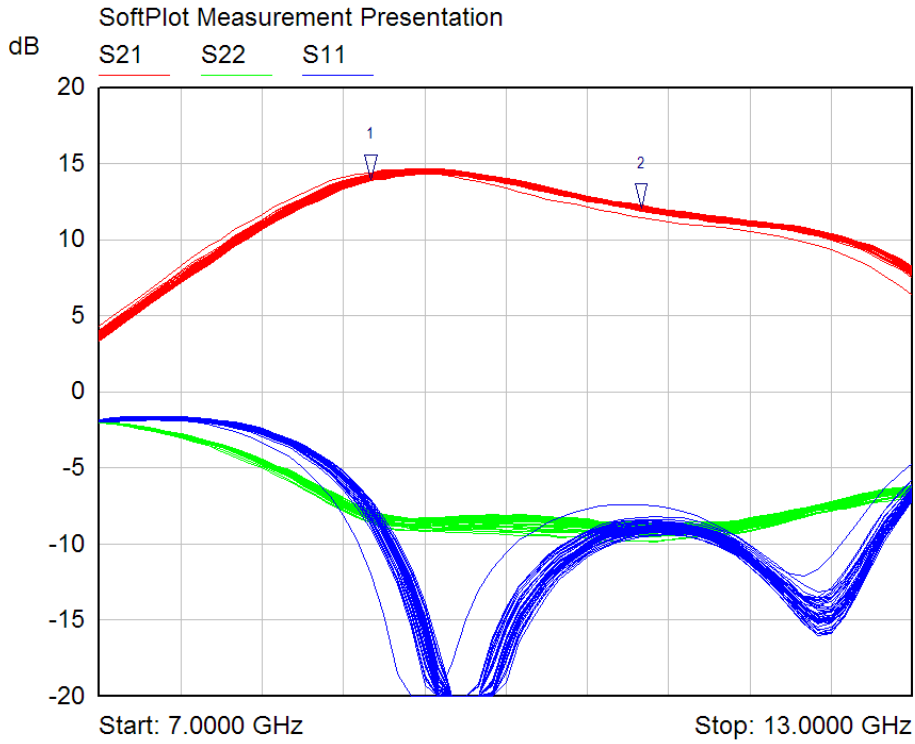


Figure 4: Die photograph of the X-band GaN PA

The s-parameters of 40 amplifiers measured on wafer at a bias of 25V Vds and 90mA Ids are plotted in Figure 5. The small signal gain is 14dB at 9GHz dropping to 12.1dB at 11GHz. A comparison of the measured to modelled small-signal performance is plotted in Figure 6. The measured results are the dotted traces and the modelled (simulated) performance is the solid traces. It can be seen that there is a slight shift up in frequency of the measured performance compared to the modelled but the agreement is good.

The large signal performance was also measured RFOV. This was measured under pulsed operation at a duty cycle of 10% with a pulse width of 25 μ s. The measured results are plotted in Figure 7 for RF input powers of 5dBm, 19dBm, 29dBm and 32dBm at a quiescent bias of 25V, 90mA. With an input power of 29dBm the RF output power is around 38.5dBm or 7W.

A corresponding plot of the PAE (Power Added Efficiency) is shown in Figure 8. At an input drive of 29dBm the PAE is around 42% from 9 to 11.5GHz with a peak value of 48%.



Mkr	Trace	X-Axis	Value	Notes
1 ▾	S21	9.0000 GHz	14.00 dB	
2 ▾	S21	11.0000 GHz	12.09 dB	

Figure 5: Measured s-parameters of 40 devices biased at 25V, 90mA

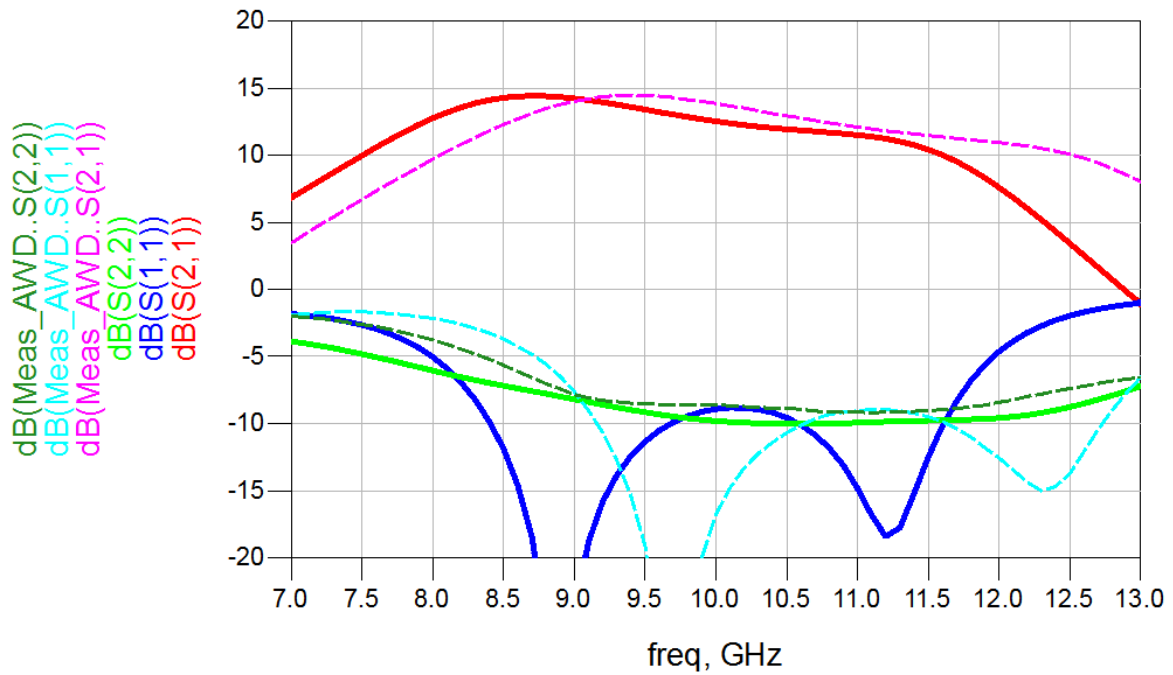


Figure 6: Comparison of measured to modelled s-parameters at 25V, 90mA bias

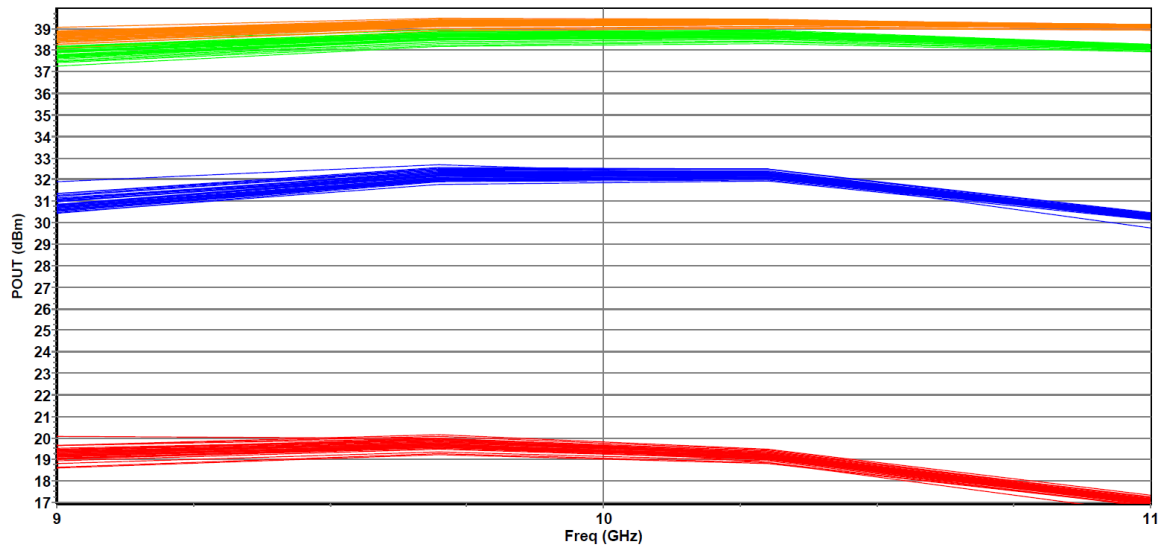


Figure 7: RFOW measured output power (10% duty, 25 μ s PW) for input powers of 5dBm, 19dBm, 29dBm and 32dBm at a quiescent bias of 25V, 90mA

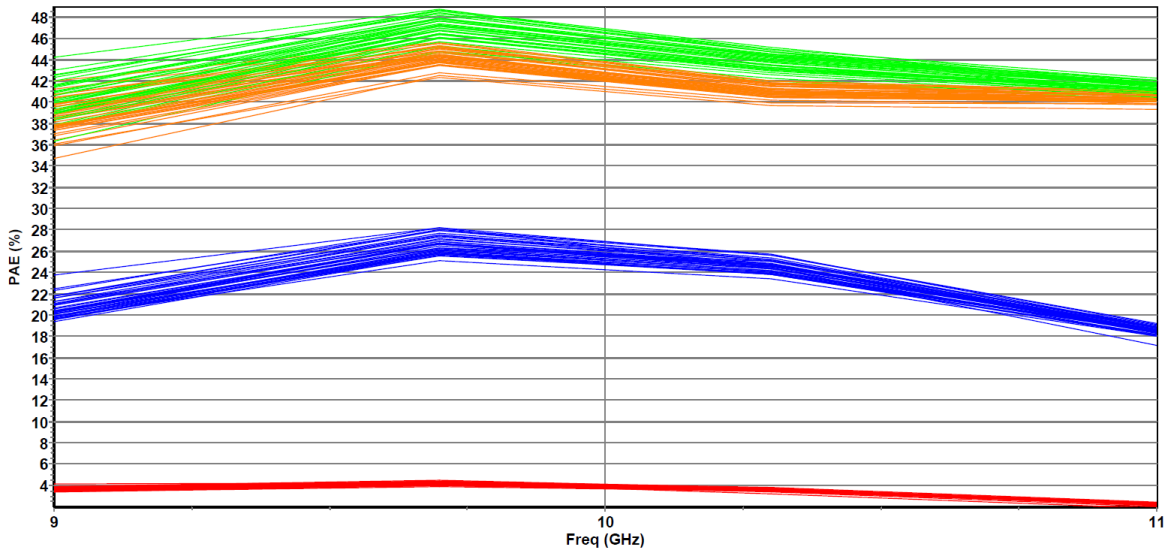


Figure 8: RFOW measured PAE (10% duty, 25 μ s PW) for input powers of 5dBm, 19dBm, 29dBm and 32dBm at a quiescent bias of 25V, 90mA

The measured and simulated power transfer characteristics at 9.7GHz are plotted in Figure 9, demonstrating very good agreement.

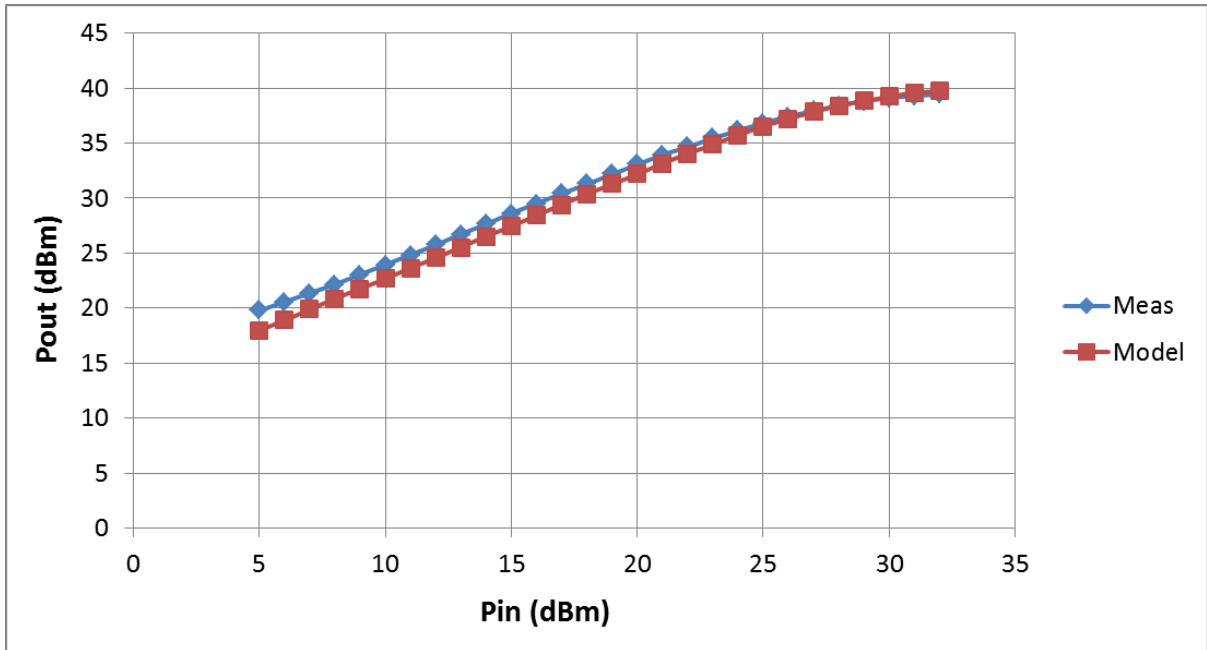


Figure 9: Measured and modelled power transfer characteristics at 9.7GHz

Summary and Conclusions

Details of the design, realisation and measured performance of a 9 to 11.5GHz GaN PA MMIC have been presented. The amplifier was realised on the GH25 GaN MMIC process of UMS and designed using the UMS PDK on ADS 2015. It was designed with active phased array radars in mind and generates an RF output power of 38.5dBm (7W) from an input drive of 29dBm with a PAE of 42%. Quiescent bias is 25V and 90mA. A summary of the measured performance of the GaN PA is presented in Table 2.

Parameter	Units	Measured	Comments
Frequency Range	GHz	9-11.5	
Small-signal gain	dB	~13	
Input return loss	dB	> 8	
Output return loss	dB	> 8	
Psat	W (dBm)	~ 7 (38.5)	+29dBm drive
PAE at Psat	%	~ 42	+29dBm drive
LS gain flatness	dB	±0.5	

Table 2: Performance summary of the GaN PA MMIC